

GE15P10**P-CHANNEL ENHANCEMENT MODE POWER MOSFET**

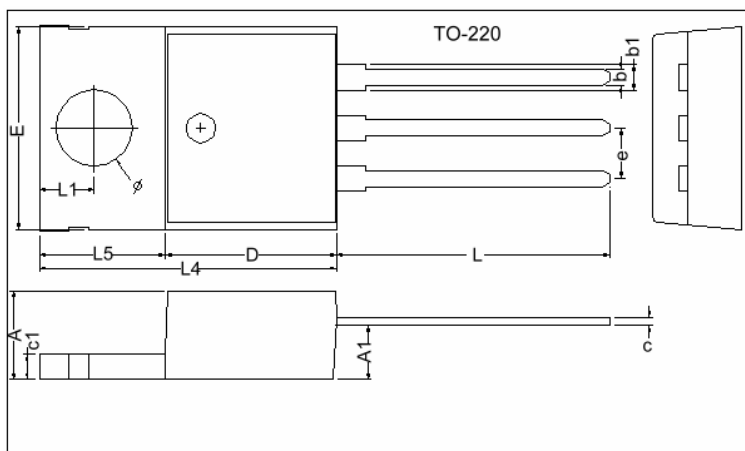
BVDSS	-100V
RDS(ON)	210mΩ
ID	-16A

Description

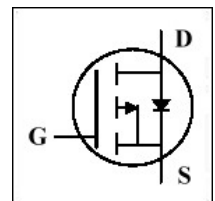
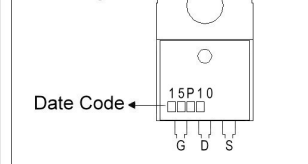
The GE15P10 (TO-220 package through-hole version) is available for low-profile applications and suited for low voltage applications such as high efficiency switching DC/DC converters and DC motor control.

Features

- *Simple Drive Requirement
- *Lower On-resistance
- *Fast Switching Characteristic
- *RoHS Compliant

Package Dimensions

Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	Ø	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=25^{\circ}C$	-16	A
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=100^{\circ}C$	-9.8	A
Pulsed Drain Current ¹	I_{DM}	-64	A
Total Power Dissipation	$P_D @T_C=25^{\circ}C$	96	W
Linear Derating Factor		0.77	W/°C
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case Max.	R_{thj-c}	1.3	°C/W
Thermal Resistance Junction-ambient Max.	R_{thj-a}	62	°C/W

Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	-100	-	-	V	V _{GS} =0, I _D =-1mA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	-	-0.1	-	V/°C	Reference to 25°C, I _D =-1mA
Gate Threshold Voltage	V _{GS(th)}	-1.0	-	-3.0	V	V _{DS} =V _{GS} , I _D =-250uA
Forward Transconductance	g _{fs}	-	8	-	S	V _{DS} =-10V, I _D =-9A
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	-25	uA	V _{DS} =-100V, V _{GS} =0
Drain-Source Leakage Current(T _j =150°C)		-	-	-100	uA	V _{DS} =-80V, V _{GS} =0
Static Drain-Source On-Resistance ²	R _{DS(ON)}	-	-	210	mΩ	V _{GS} =-10V, I _D =-9A
Total Gate Charge ²	Q _g	-	37	60	nC	I _D =-9A V _{DS} =-80V V _{GS} =-10V
Gate-Source Charge	Q _{gs}	-	5	-		
Gate-Drain ("Miller") Charge	Q _{gd}	-	15	-		
Turn-on Delay Time ²	T _{d(on)}	-	11	-	ns	V _{DS} =-50V I _D =-9A V _{GS} =-10V R _G =10Ω R _D =5.6Ω
Rise Time	T _r	-	25	-		
Turn-off Delay Time	T _{d(off)}	-	56	-		
Fall Time	T _f	-	36	-		
Input Capacitance	C _{iss}	-	1180	1900	pF	V _{GS} =0V V _{DS} =-25V f=1.0MHz
Output Capacitance	C _{oss}	-	250	-		
Reverse Transfer Capacitance	C _{rss}	-	75	-		
Gate Resistance	R _g	-	3.6	5	Ω	f=1.0MHz

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V _{SD}	-	-	-1.3	V	I _S =-9A, V _{GS} =0V
Reverse Recovery Time ²	T _{rr}	-	95	-	ns	I _S =-9A, V _{GS} =0V di/dt=100A/μs
Reverse Recovery Charge	Q _{rr}	-	410	-	nC	

Notes: 1. Pulse width limited by safe operating area.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

Characteristics Curve

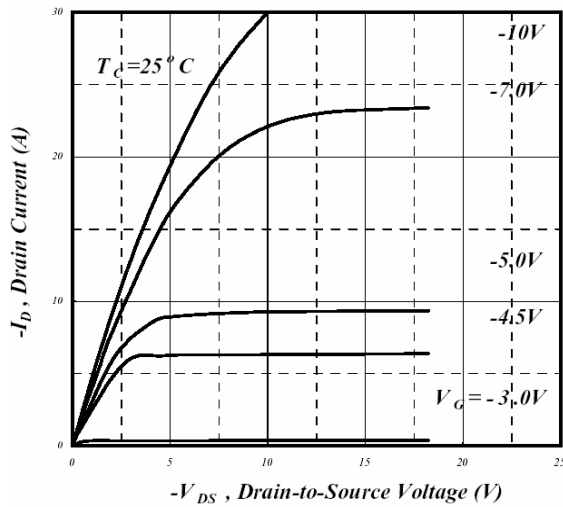


Fig 1. Typical Output Characteristics

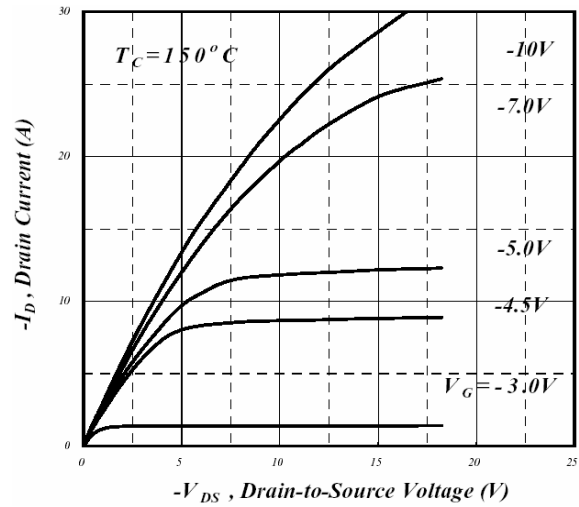


Fig 2. Typical Output Characteristics

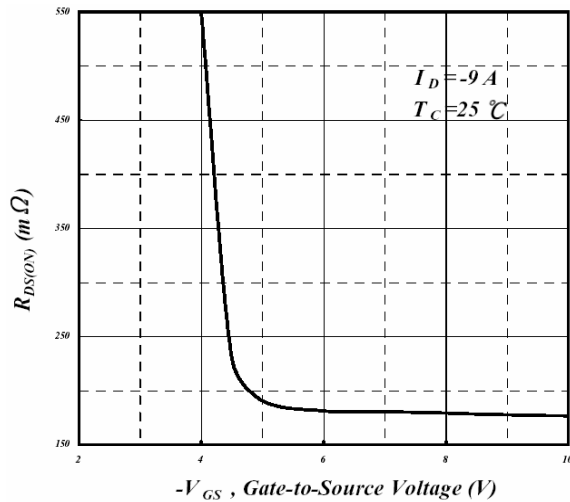


Fig 3. On-Resistance v.s. Gate Voltage

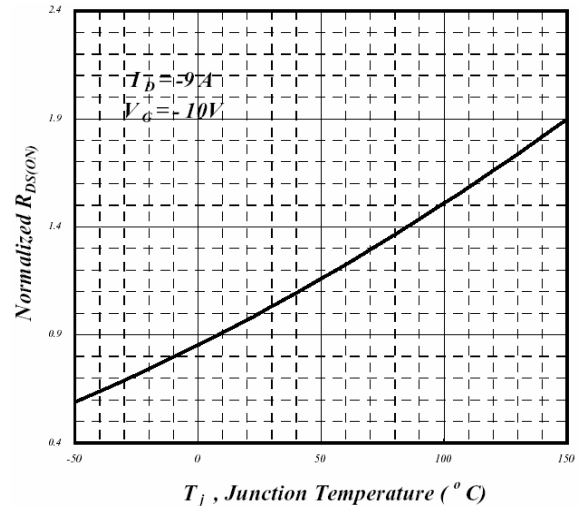


Fig 4. Normalized On-Resistance v.s. Junction Temperature

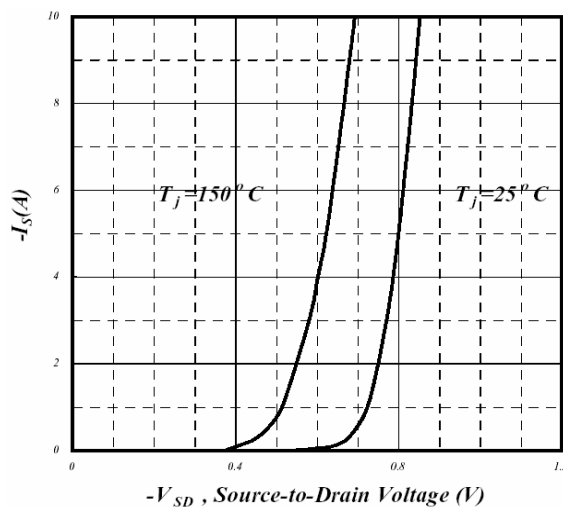


Fig 5. Forward Characteristics of Reverse Diode

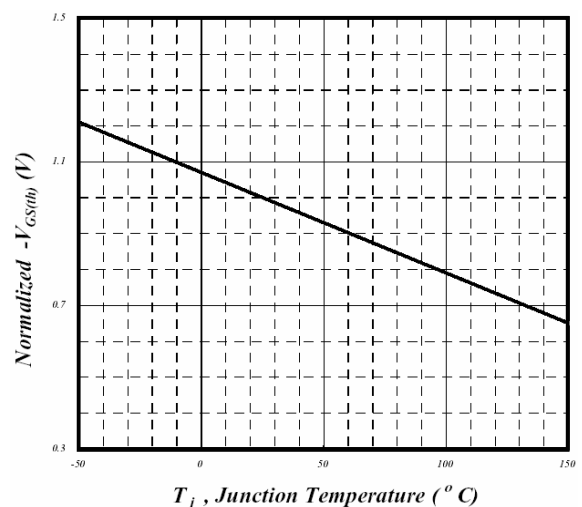


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

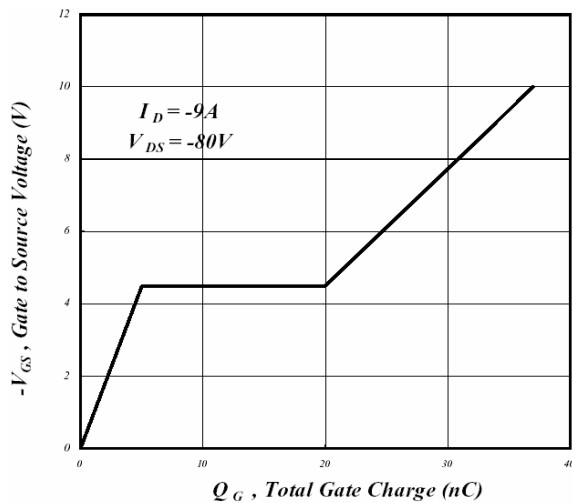


Fig 7. Gate Charge Characteristics

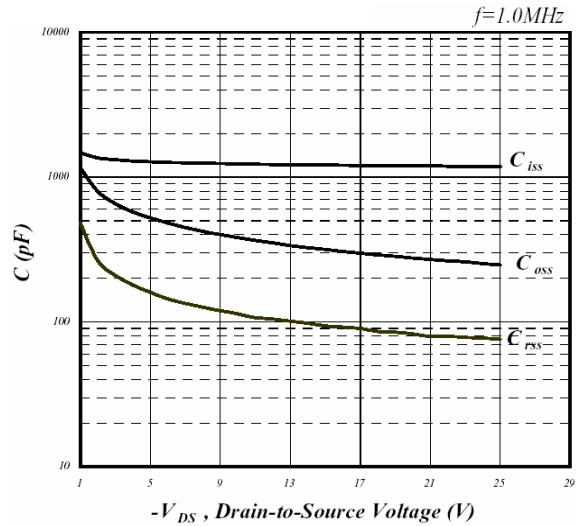


Fig 8. Typical Capacitance Characteristics

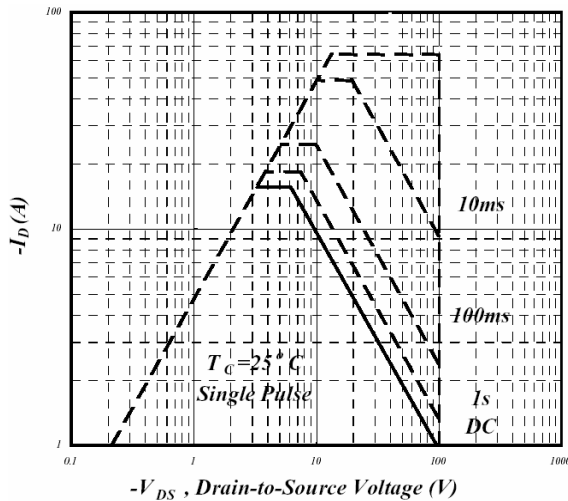


Fig 9. Maximum Safe Operating Area

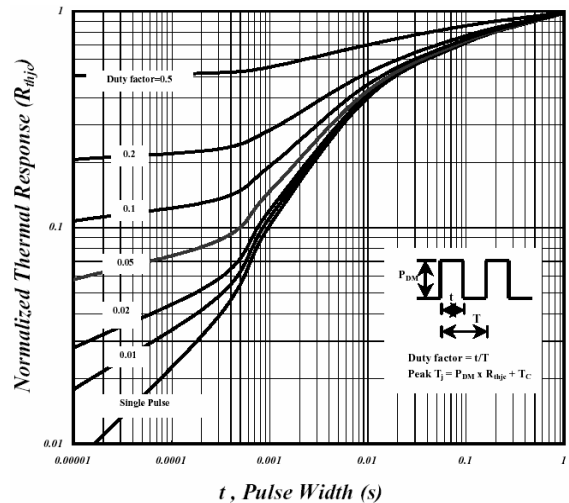


Fig 10. Effective Transient Thermal Impedance

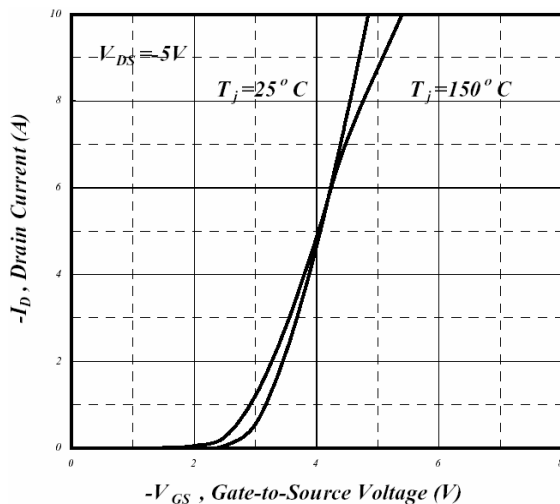


Fig 11. Transfer Characteristics

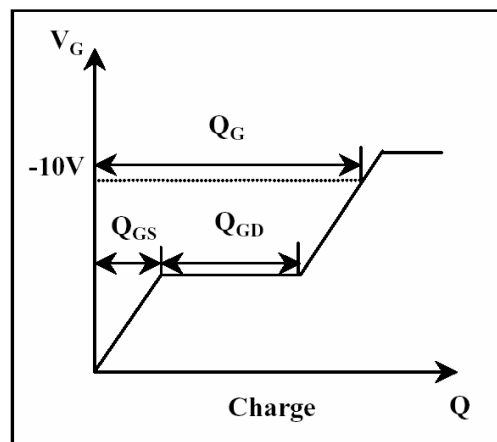


Fig 12. Gate Charge Waveform

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